

CD4011A, CD4012A, CD4023A Types

CMOS NAND Gates

Quad 2 Input – CD4011A

Dual 4 Input – CD4012A

Triple 3 Input – CD4023A

The TI-CD4011A, CD4012A, and CD4023A NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of CMOS gates.

These types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

MAXIMUM RATINGS, Absolute-Maximum Values:

STORAGE-TEMPERATURE RANGE (T_{stg}) -65 to +150°C

OPERATING-TEMPERATURE RANGE (T_A):

PACKAGE TYPES D, F, K, H -65 to +125°C

PART NUMBER E -40 to +85°C

DC SUPPLY-VOLTAGE RANGE, (V_{DD}):

(Voltages referenced to V_{SS} Terminal): -0.5 to +15 V

POWER DISSIPATION PER PACKAGE (P_D):

FOR $T_A = -40$ to $+60^\circ\text{C}$ (PACKAGE TYPE E) 500 mW

FOR $T_A = +60$ to $+85^\circ\text{C}$ (PACKAGE TYPE E) Derate Linearly at $12 \text{ mW}/^\circ\text{C}$ to 200 mW

FOR $T_A = -55$ to $+100^\circ\text{C}$ (PACKAGE TYPES D, F, K) 500 mW

FOR $T_A = +100$ to $+125^\circ\text{C}$ (PACKAGE TYPES D, F, K) Derate Linearly at $12 \text{ mW}/^\circ\text{C}$ to 200 mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR:

FOR $T_A = \text{FULL PACKAGE TEMPERATURE RANGE (ALL PACKAGE TYPES)}$ 100 mW

INPUT VOLTAGE RANGE, ALL INPUTS -0.5 to $V_{DD} + 0.5$ V

LEAD TEMPERATURE (DURING SOLDERING):

At distance $1/16 \pm 1/32$ inch (1.69 ± 0.79 mm) from case for 10 s max $+265^\circ\text{C}$

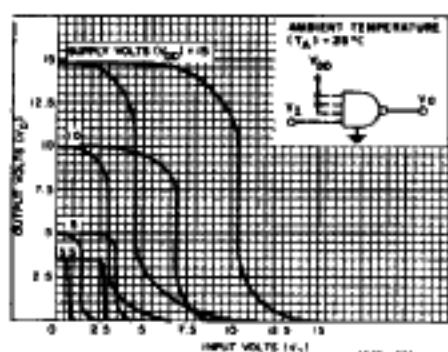


Fig. 2 – Minimum & maximum voltage transfer characteristics.

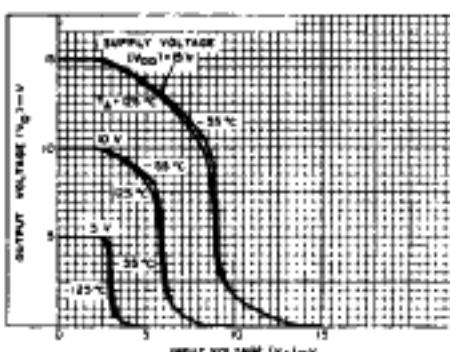


Fig. 3 – Typical voltage transfer characteristics as a function of temperature.

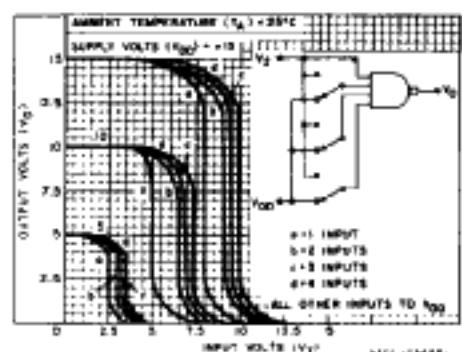


Fig. 4 – Typical multiple input switching transfer characteristics for CD4012A.

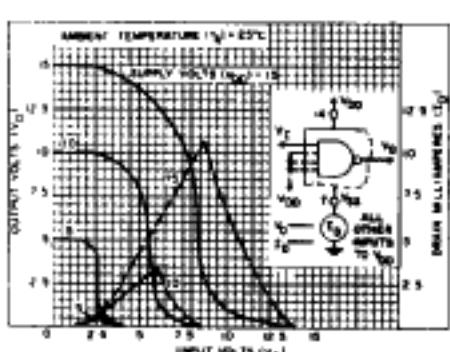
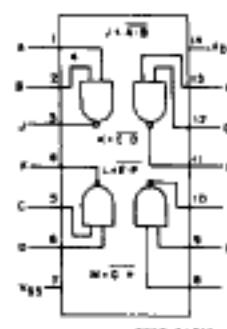
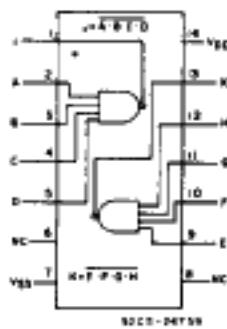


Fig. 5 – Typical current & voltage transfer characteristics.

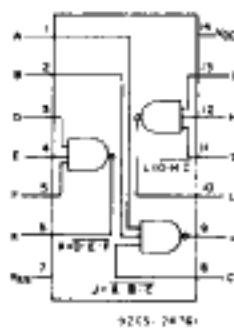
TEXAS INSTRUMENTS
Data sheet acquired from Harris Semiconductor
SCHS313



CD4011A

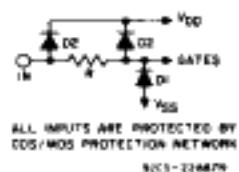


CD4012A



CD4023AH

Fig. 1 – Functional diagrams.



ALL INPUTS ARE PROTECTED BY
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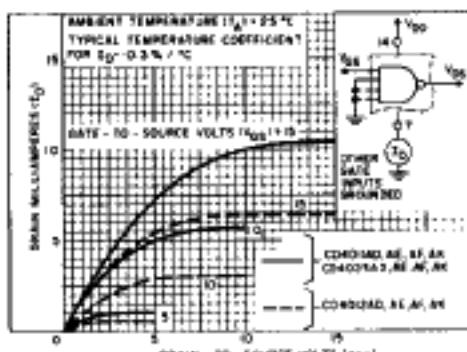
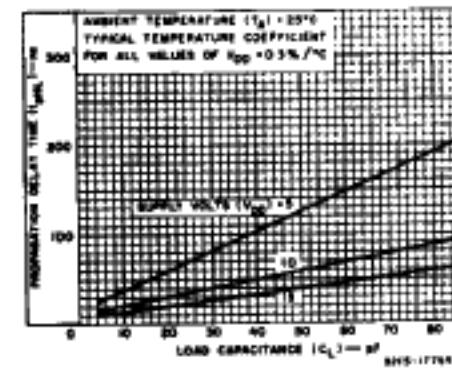
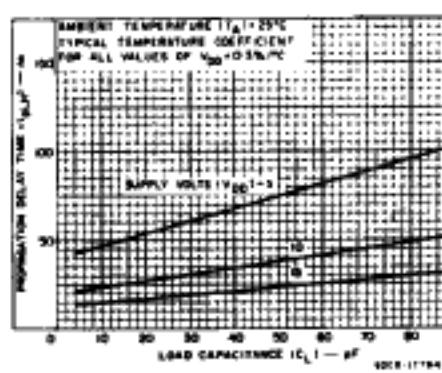
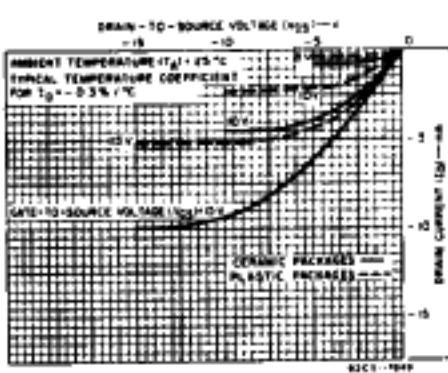
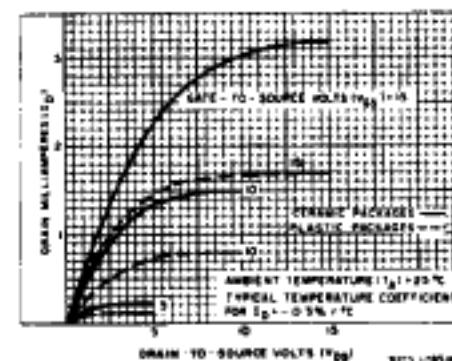
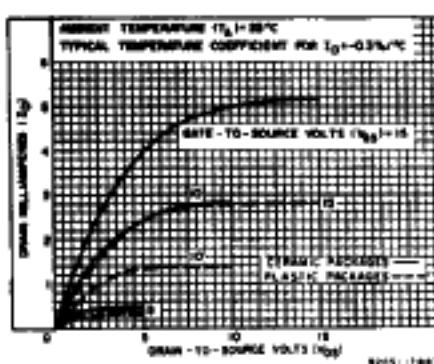
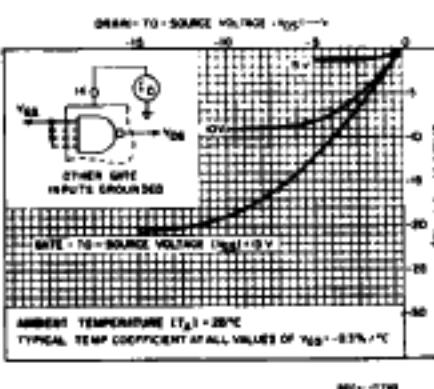


Fig. 6 – Typical n-channel drain characteristics.

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STATIC ELECTRICAL CHARACTERISTICS

Characteristic	Conditions			Limits at Indicated Temperatures (°C)								Units
				D,F,K,H Packages				E Package				
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	+25	+125	-40	+25	+85			
Quiescent Device Current, I _L Max.	-	-	5	0.05	0.001	0.05	3	0.5	0.005	0.5	15	μA
	-	-	10	0.1	0.001	0.1	6	5	0.006	5	30	
	-	-	15	2	0.02	2	40	50	0.5	50	500	
Output Voltage: Low-Level VOL	-	0.5	5	0 Typ.; 0.05 Max.								V
	-	0.10	10	0 Typ.; 0.05 Max.								
High Level, V _{OH}	-	0.5	5	4.95 Min.; 5 Typ.								V
	-	0.10	10	9.95 Min.; 10 Typ.								
Noise Immunity: Inputs Low, V _{NL}	3.6	-	5	1.5 Min.; 2.25 Typ.								V
	7.2	-	10	3 Min.; 4.5 Typ.								
Inputs High, V _{NH}	1.4	-	5	1.5 Min.; 2.25 Typ.								V
	2.8	-	10	3 Min.; 4.5 Typ.								
Noise Margin: Inputs Low, V _{NML}	4.5	-	5	1 Min.								V
	9	-	10	1 Min.								
Inputs High, V _{NMH}	0.5	-	5	1 Min.								V
	1	-	10	1 Min.								
Output Drive Current: N-Channel (Sink) I _{DN} Min. CD4011A												mA
	0.5	-	5	0.31	0.5	0.25	0.175	0.145	0.5	0.12	0.095	
	0.5	-	10	0.62	0.6	0.5	0.35	0.3	0.6	0.25	0.2	
CD4012A	0.5	-	5	0.15	0.25	0.12	0.085	0.072	0.25	0.06	0.05	mA
	0.5	-	10	0.31	0.6	0.25	0.175	0.155	0.6	0.13	0.105	
P-Channel (Source), I _D ^P Min. All Types	4.5	-	5	-0.31	-0.5	-0.25	-0.175	-0.145	-0.5	-0.12	-0.095	mA
	9.5	-	10	-0.75	-1.2	-0.6	-0.4	-0.35	-1.2	-0.3	-0.24	
Input Leakage Current, I _{IL} , I _{IH}	Any Input	15	$\pm 10^{-5}$ Typ.; ± 1 Max.								μA	



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DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$, $C_L = 15 \text{ pF}$, Input $t_r, t_f = 20 \text{ ns}$, $R_L = 200 \text{ k}\Omega$

CHARACTERISTICS	TEST CONDITIONS	LIMITS				UNITS	
		D, F, K, H Packages		E Package			
		V _{DD} (V)	Typ.	Max.	Typ.	Max.	
Propagation Delay Time: Low-to-High Level, t_{PLH}		5	50	75	50	100	ns
		10	25	40	25	50	
High-to-Low Level, t_{PHL} CD4011A and CD4023A		5	50	75	50	100	ns
		10	25	40	25	50	
CD4012A		5	100	150	100	200	ns
		10	50	75	50	100	
Transition Time: Low-to-High Level, t_{TLH}		5	75	100	75	125	ns
		10	40	60	40	75	
High-to-Low Level, t_{THL} CD4011A and CD4023A		5	75	125	75	150	ns
		10	50	75	50	100	
CD4012A		5	250	375	250	500	ns
		10	125	200	125	250	
Input Capacitance, C_I	Any Input	5	—	5	—	pF	

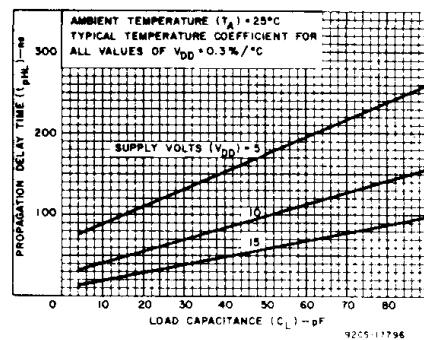


Fig. 13 — Typical high-to-low level propagation delay time vs. C_L — CD4012A.

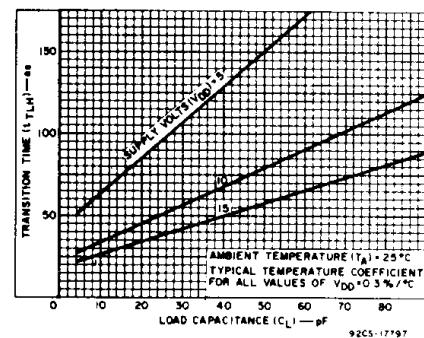


Fig. 14 — Typical low-to-high transition time vs. C_L .

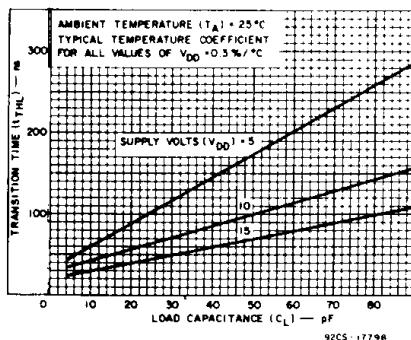


Fig. 15 — Typical high-to-low level transition time vs. C_L — CD4011A & CD4023A.

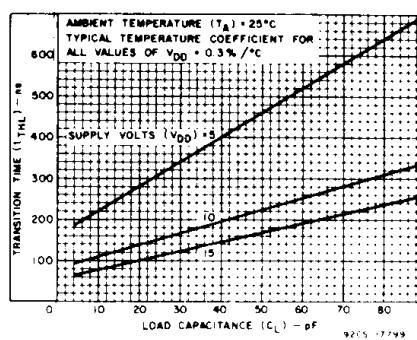


Fig. 16 — Typical high-to-low level transition time vs. C_L — CD4012A.

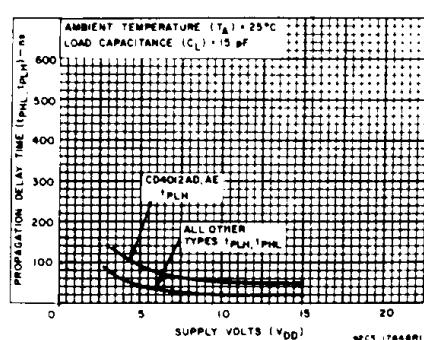


Fig. 17 — Minimum propagation delay time vs. V_{DD} .

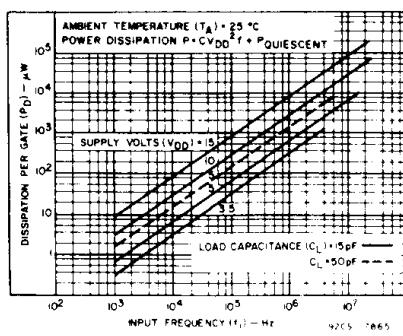


Fig. 18 — Typical dissipation characteristics.

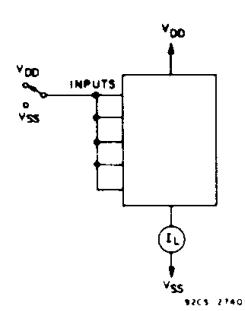


Fig. 19 — Quiescent device current test circuit.

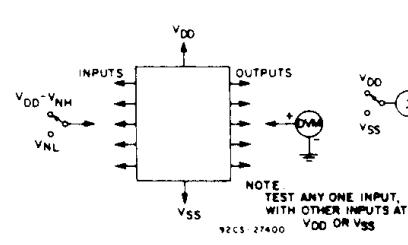


Fig. 20 — Noise immunity test circuit.

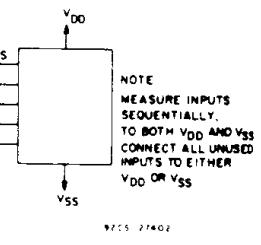


Fig. 21 — Input leakage current test circuit.

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